

isc Silicon NPN Power Transistor

2N6574

DESCRIPTION

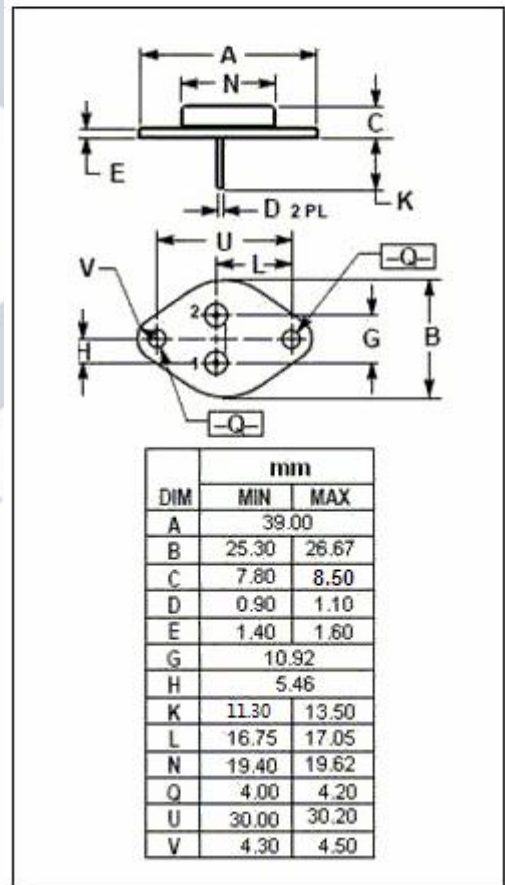
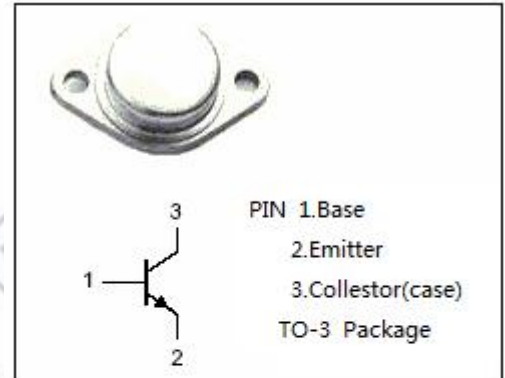
- Collector-Emitter Sustaining Voltage-
: $V_{CEO} = 275V(\text{Min.})$
- Fast Switching Speed
- Low Collector Saturation Voltage-
: $V_{CE(\text{sat})} = 1.5V(\text{Max.}) @ I_C = 25A$

APPLICATIONS

- Designed for converters, inverters, pulse-width- modulated regulators and a variety of power switching circuits.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	275	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	10	A
P_C	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	125	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2N6574****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3A; I_B=0.3A$		1	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=7A; V_{CE}=3V$		1.4	V
I_{EBO}	Emitter Cutoff Current	$V_{EB}=8V; I_C=0$		0.1	mA
h_{FE-1}	DC Current Gain	$I_C=3A; V_{CE}=3V$	20	60	
h_{FE-2}	DC Current Gain	$I_C=7A; V_{CE}=3V$	7	21	
C_{OB}	Collector Output Capacitance	$I_E=0; V_{CB}=10V; f_{test}=0.1\text{MHz}$			pF
f_T	Current Gain-Bandwidth Product	$I_C=1A; V_{CE}=10V$	5		MHz

Switching times

T_{on}	On Time	$I_C=7A; I_B=1.4A,$		1	μs
t_{off}	Off Time			3.2	μs